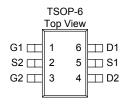
N & P-Channel 40-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r _{DS(on)} provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY							
$V_{DS}(V)$ $r_{DS(on)}(\Omega)$ $I_{D}(A)$							
40	$0.063 @V_{CS} = 10V$	3.7					
40	$0.082 @V_{CS} = 4.5V$	3.3					
-40	$0.172 @V_{CS} = -10V$	-2.7					
	$0.240 @V_{CS} = -4.5V$	-2.2					







ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)									
Parameter	Symbol	N-Channel	P-Channel	Units					
Drain-Source Voltage			40	-40	V				
Gate-Source Voltage	V_{GS}	±20	±20	V					
	$T_A=25^{\circ}C$	T	3.7	-2.7					
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	I_{D}	2.9	-2.1	Α				
Pulsed Drain Current ^b	I_{DM}	8	-8						
Continuous Source Current (Diode Conduc	I_S	1.05	-1.05	A					
D a	$T_A=25^{\circ}C$	D	1.	W					
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$P_{\rm D}$	0.7						
Operating Junction and Storage Temperature Range			-55 to	°C					

THERMAL RESISTANCE RATINGS								
Domomotou	Symbol	N-Channel		P-Channel		TI:4		
Parameter		Тур	Max	Тур	Max	Unit		
Mariana Innation to Analysis a	t <= 10 sec	D	93	110	93	110	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	130	150	130	150	T C/W	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

AM3548C

Dav4	C11	Took Co. 1'4'		Li	mits		TT •4	
Parameter	Symbol	Test Conditions	Ch	Min	Тур	Max	Unit	
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	VGS = VDS, $ID = 250 uA$	N	1			V	
Gate-Tilleshold Voltage	V GS(th)	VGS = VDS, $ID = -250 uA$	P	-1			·	
Gate-Body Leakage Current	I_{GSS}	VDS = 0 V, $VGS = 20 V$	N			100	uA	
Gate-Body Leakage Current	1055	$V_{DS} = 0 \text{ V}, V_{GS} = -20 \text{ V}$	P			-100	uA	
		VDS = 32 V, VGS = 0 V	N			1	uA	
Zero Gate Voltage Drain Current	I_{DSS}	VDS = -32 V, VGS = 0 V	P			-1	ui I	
Zero Gate Voltage Diam Current	1088	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ} \text{C}$	N			10	uА	
		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$	P			-10	u/ t	
On-State Drain Current ^A	ī	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N	5				
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	P	-5			A	
		VGS = 10 V, ID = 3.7 A	N			0.063		
Drain-Source On-Resistance ^A		VGS = -10 V, ID = 3.1 A	P			0.172	Ω	
Diam-Source On-Resistance	$r_{\mathrm{DS(on)}}$	VGS = 4.5 V, ID = 3.3 A	N			0.082	52	
		VGS = -4.5 V, ID = -2.2 A	P			0.240		
Forward Tranconductance ^A	\mathbf{g}_{fs}	$V_{DS} = 5 \text{ V}, I_D = 3.7 \text{ A}$	N		10		S	
Forward Tranconductance	SIS	$V_{DS} = -5 \text{ V}, I_D = 3.1 \text{ A}$	P		5			
D: 1 E 1W 1 A	V	$I_S = 1.05 \text{ A}, V_{GS} = 0 \text{ V}$	N		0.80		S	
Diode Forward Voltage ^A	$ m V_{SD}$	$I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$	P		-0.83		5	
Dynamic ^b			•					
Total Gate Charge	Q_g		N		2.2			
Total Gate Charge	Qg	N-Channel	N-Channel P 3.8	3.8]		
Gate-Source Charge	Q_{gs}	V_{DS} =15V, V_{GS} =4.5V, I_{D} =2.7A	N		0.5		nC	
Gute-Bource Charge	≺gs	P-Channel	P		0.6			
Gate-Drain Charge	Q_{ed}	VDS=-15V, VGS=-4.5V, ID=-3.1A	N		0.8			
	₹gu		P		1.5			
Turn-On Delay Time	$t_{d(on)}$		N		5		-	
	t _r	N-Chaneel	P				ļ	
Rise Time		V_{DD} =15V, VGS=4.5V, ID=1A, R_{GEN} =15 Ω ,	N P		12		nS	
		R _{GEN} =1512, P-Channel	N N		13			
Turn-Off Delay Time	$t_{d(off)}$	VDD=-15V, VGS=-4.5V, ID=-1A	P		20			
		RGEN=15 Ω	N		7		1	
Fall-Time	t_{f}		P	1	20	 	1	

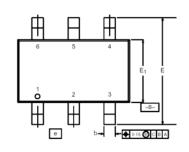
Notes

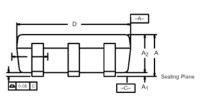
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

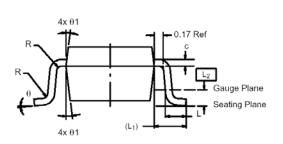
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Package Information

TSOP-6: 6LEAD







	MIL	LIMET	ERS	INCHES				
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.91	-	1.10	0.036	-	0.043		
A ₁	0.01	_	0.10	0.0004	_	0.004		
A ₂	0.84	_	1.00	0.033	0.038	0.039		
b	0.30	0.32	0.45	0.012	0.013	0.018		
С	0.10	0.15	0.20	0.004	0.006	0.008		
D	2.95	3.05	3.10	0.116	0.120	0.122		
E	2.70	2.85	2.98	0.106	0.112	0.117		
E ₁	1.55	1.65	1.70	0.061	0.065	0.067		
е		1.00 BSC		0.0394 BSC				
L	0.35	_	0.50	0.014	-	0.020		
L ₁		0.60 Ref		0.024 Ref				
L ₂		0.25 BSC		0.010 BSC				
R	0.10	_	_	0.004	_	_		
θ	0°	4°	8°	0°	4°	8°		
θ_1		7° Nom			7° Nom			